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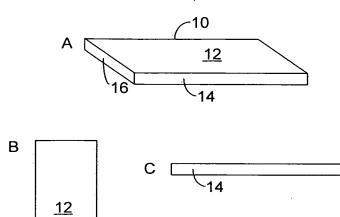
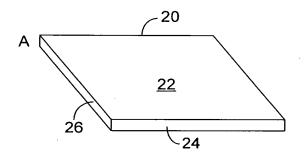


FIG. 1



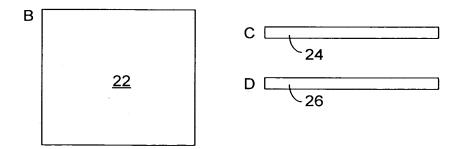


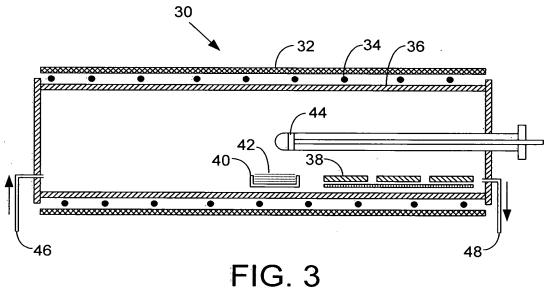
FIG. 2

## SEMICONDUCTING OXIDE NANOSTRUCTURES

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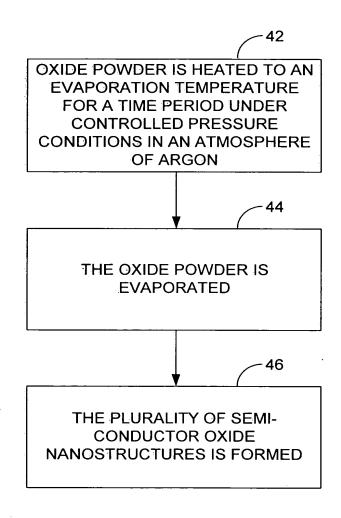


FIG. 4



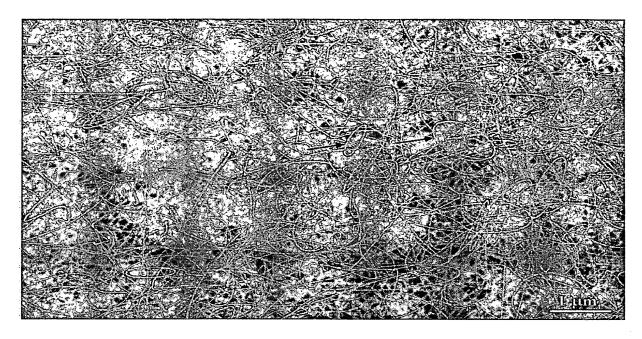
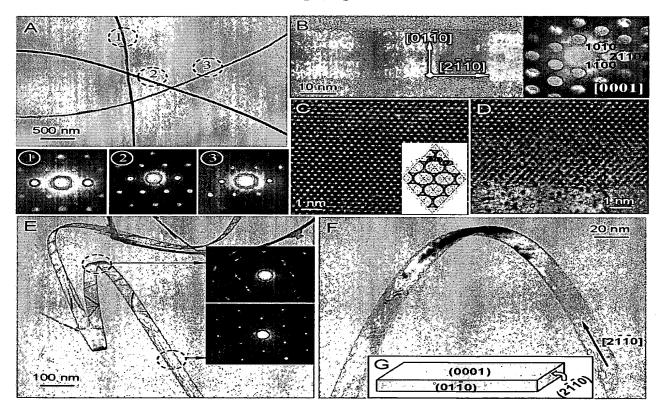
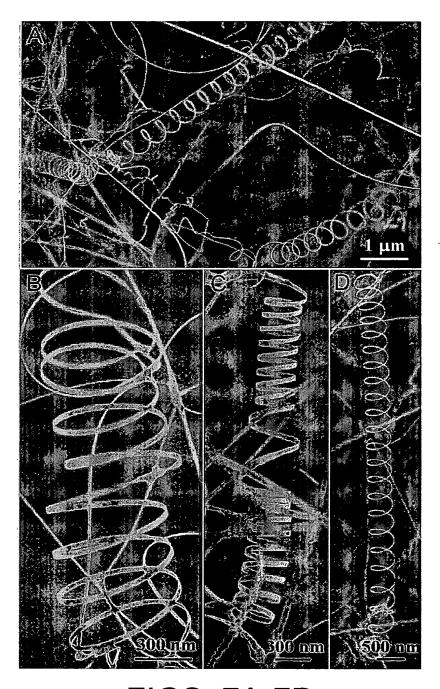


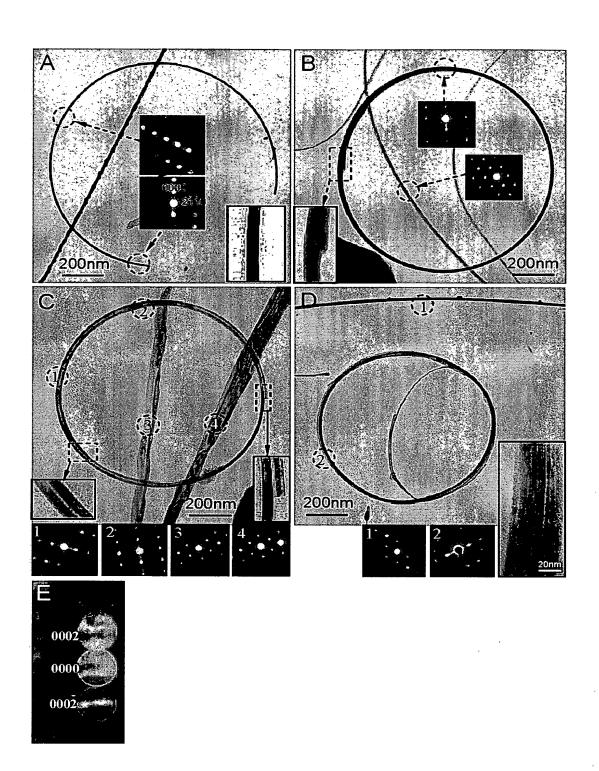
FIG. 5



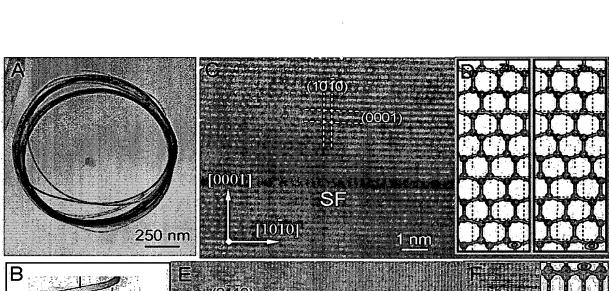
FIGS. 6A-6G

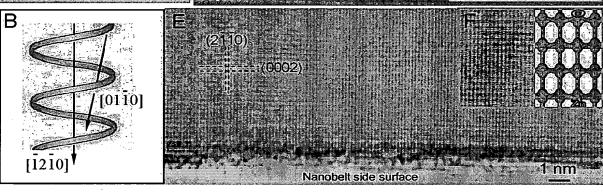


FIGS. 7A-7D

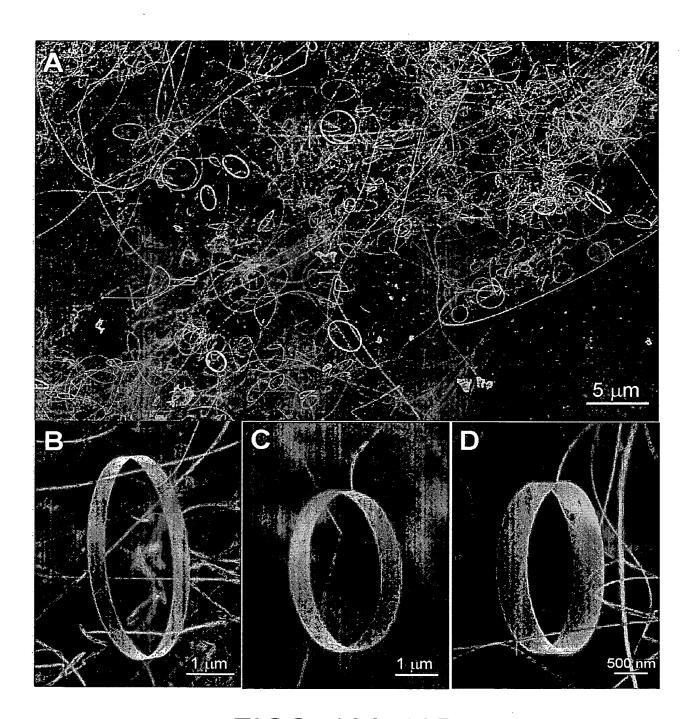


FIGS. 8A-8E

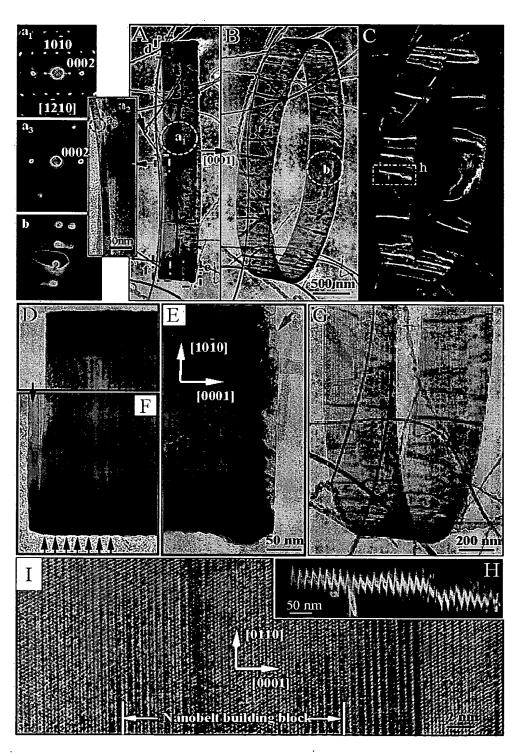




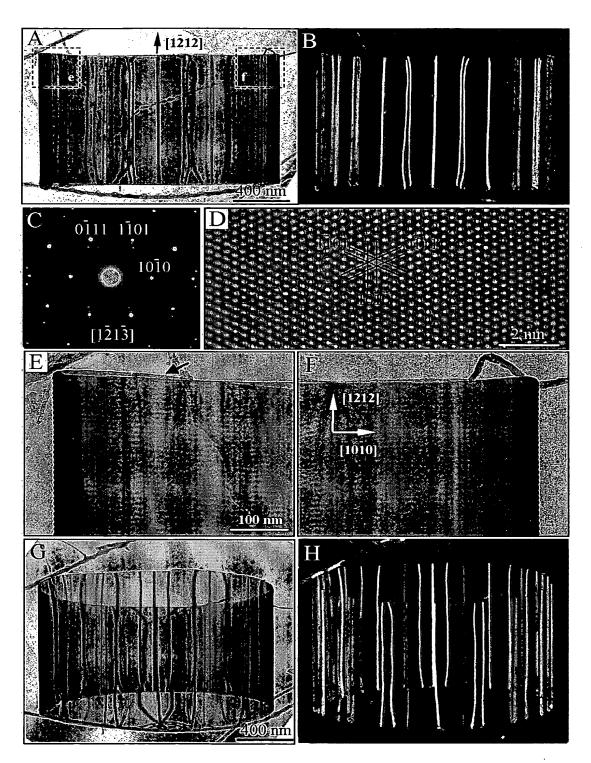
FIGS. 9A-9F



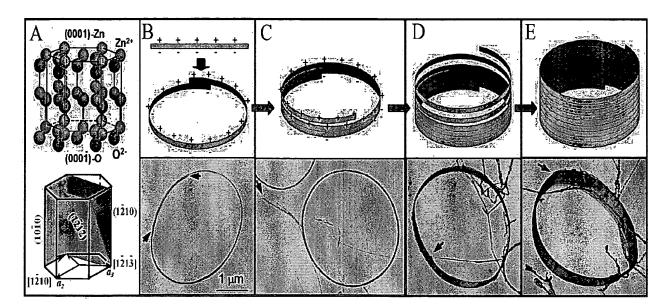
FIGS. 10A-10D



FIGS. 11A-11I



FIGS. 12A-12H



FIGS. 13A-13E